

**DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

**Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max     | I <sub>D</sub> Max<br>T <sub>A</sub> = +25°C |
|-------------------|-----------------------------|--|
| 60V               | 2Ω @ V <sub>GS</sub> = 10V  | 305mA  |
|                   | 3Ω @ V <sub>GS</sub> = 4.5V | 249mA  |

**Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- General-purpose interfacing switches
- Power-management functions
- Analog switches

**Features and Benefits**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface-Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN601VKQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

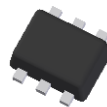
<https://www.diodes.com/quality/product-definitions/>

**Mechanical Data**

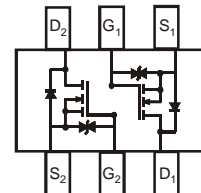
- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.003 grams (Approximate)



SOT563



Top View



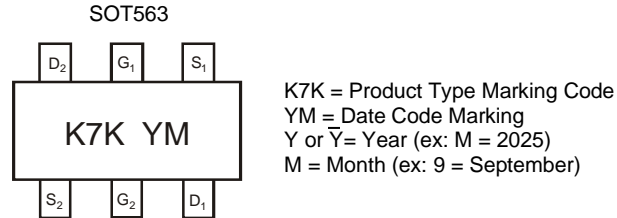
Top View  
Internal Schematic

**Ordering Information** (Note 4)

| Orderable Part Number | Package | Packing |             |
|-----------------------|---------|---------|-------------|
|                       |         | Qty.    | Carrier     |
| DMN601VKQ-7           | SOT563  | 3,000   | Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



### Date Code Key

| Month | 2005 | ... | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 | 2031 | 2032 | 2033 | 2034 |
|-------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code  | S    | ... | M    | N    | P    | R    | S    | T    | U    | V    | W    | X    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic         | Symbol           | Value | Unit |
|------------------------|------------------|-------|------|
| Drain-Source Voltage   | V <sub>DSS</sub> | 60    | V    |
| Gate-Source Voltage    | V <sub>GSS</sub> | ±20   | V    |
| Drain Current (Note 5) | Continuous       | 305   | mA   |
|                        | Pulsed (Note 6)  | 800   |      |

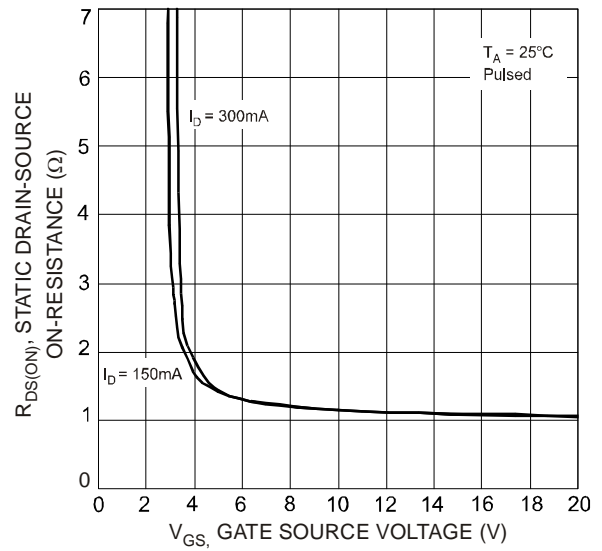
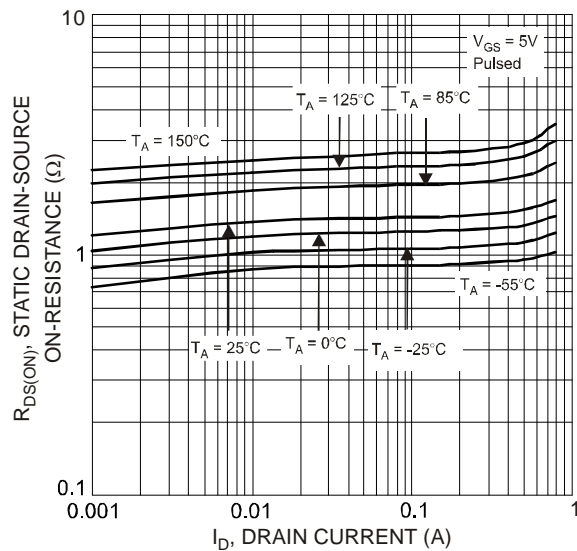
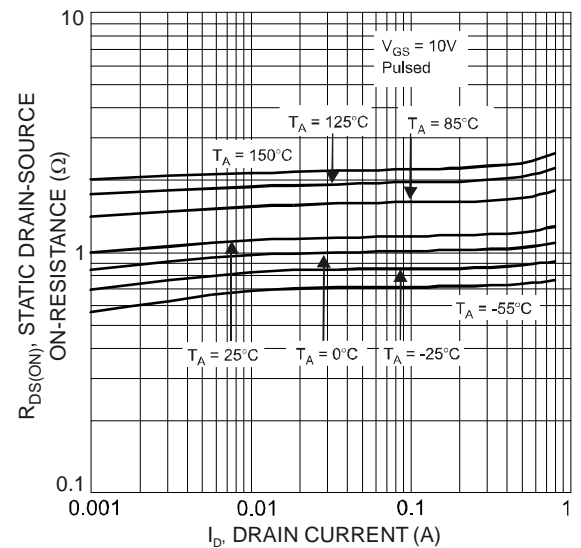
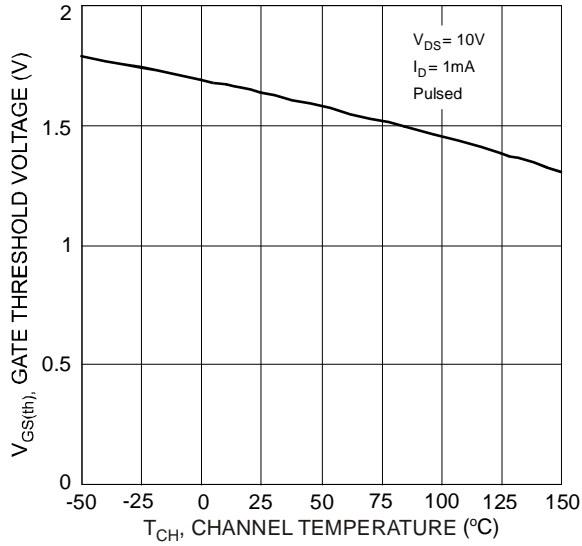
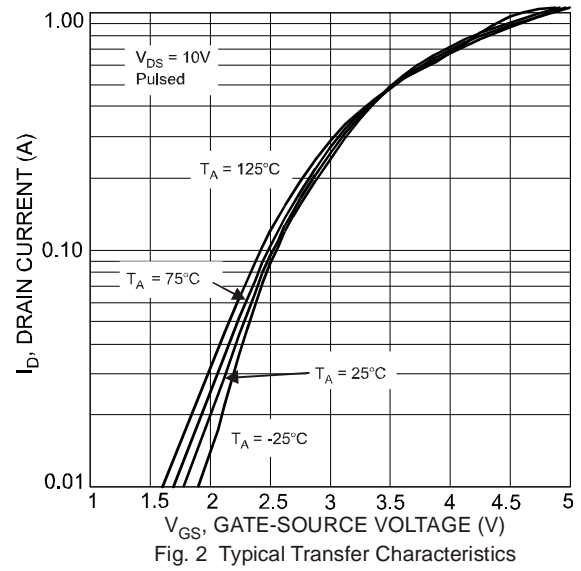
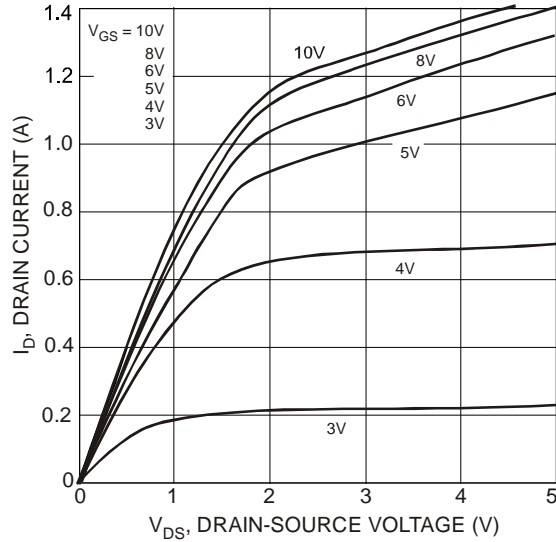
## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                          | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)        | P <sub>D</sub>                    | 250         | mW   |
| Thermal Resistance, Junction to Ambient | R <sub>θJA</sub>                  | 500         | °C/W |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -65 to +150 | °C   |

## Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                    | Symbol              | Min | Typ | Max  | Unit | Test Condition   |
|-----------------------------------|---------------------|-----|-----|------|------|--|
| OFF CHARACTERISTICS (Note 7)      |                     |     |     |      |      |  |
| Drain-Source Breakdown Voltage    | BV <sub>DSS</sub>   | 60  | —   | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA                |
| Zero Gate Voltage Drain Current   | I <sub>DSS</sub>    | —   | —   | 250  | nA   | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V                |
| Gate-Source Leakage               | I <sub>GSS</sub>    | —   | —   | ±500 | nA   | V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V               |
|                                   |                     | —   | —   | ±100 |      | V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V                |
| ON CHARACTERISTICS (Note 7)       |                     |     |     |      |      |  |
| Gate Threshold Voltage            | V <sub>GS(th)</sub> | 1.0 | 1.6 | 2.5  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA |
| Static Drain-Source On-Resistance | R <sub>DS(ON)</sub> | —   | 1.3 | 2    | Ω    | V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5A               |
|                                   |                     | —   | 1.5 | 3    |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> =0.2A               |
| Forward Transfer Admittance       | Y <sub>fs</sub>     | —   | 284 | —    | ms   | V <sub>DS</sub> =10V, I <sub>D</sub> = 0.2A                |
| Diode Forward Voltage (Note 7)    | V <sub>SD</sub>     | 0.5 | 0.8 | 1.4  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA               |
| DYNAMIC CHARACTERISTICS           |                     |     |     |      |      |  |
| Input Capacitance                 | C <sub>iss</sub>    | —   | —   | 50   | pF   | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V<br>f = 1.0MHz  |
| Output Capacitance                | C <sub>oss</sub>    | —   | —   | 25   | pF   |  |
| Reverse Transfer Capacitance      | C <sub>rss</sub>    | —   | —   | 5.0  | pF   |  |

- Notes: 5. Device mounted on FR-4 PCB.  
 6. Pulse width ≤10μs, Duty Cycle ≤1%.  
 7. Short duration pulse test used to minimize self-heating effect.



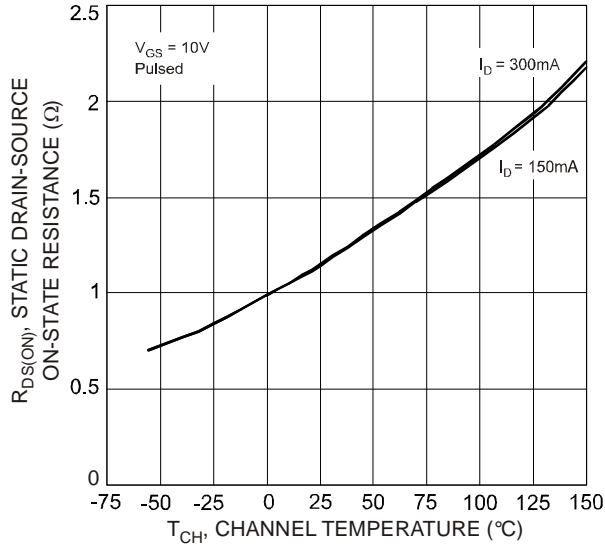


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

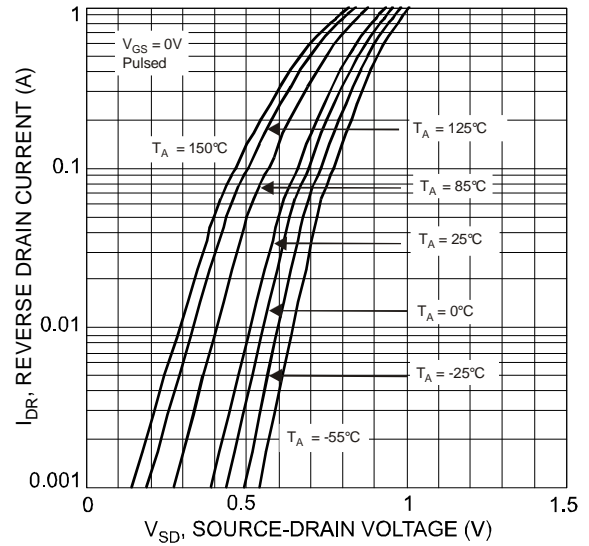


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

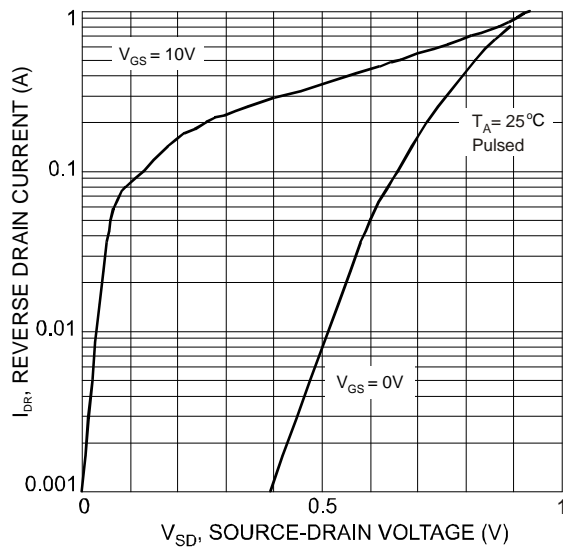


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

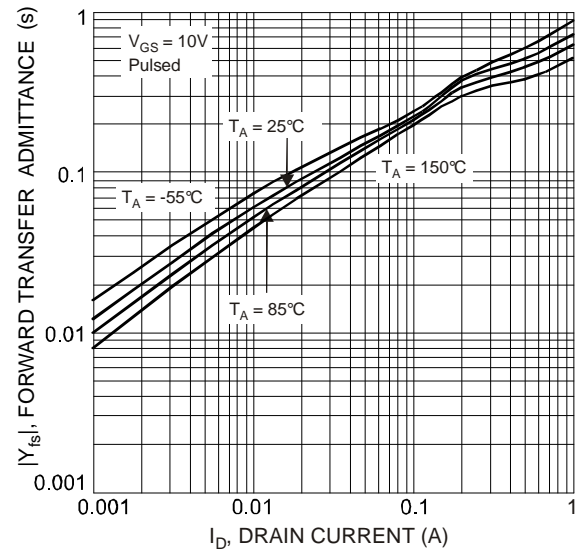
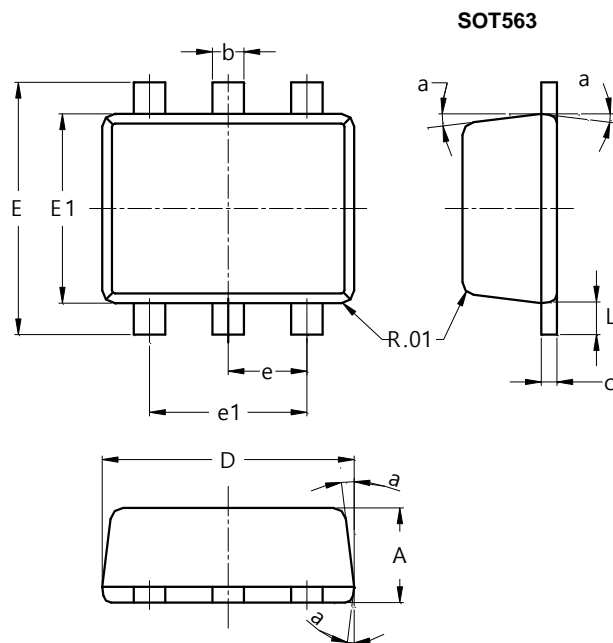


Fig. 10 Forward Transfer Admittance vs. Drain Current

## Package Outline Dimensions

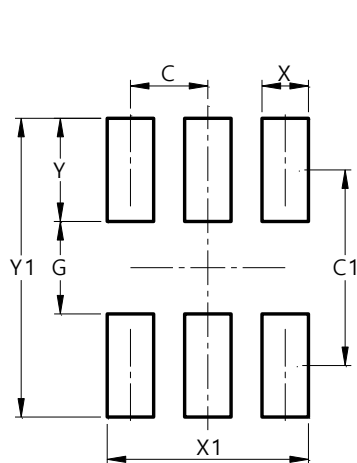
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



| SOT563               |      |      |      |
|----------------------|------|------|------|
| Dim                  | Min  | Max  | Typ  |
| <b>A</b>             | 0.55 | 0.60 | --   |
| <b>b</b>             | 0.15 | 0.30 | 0.20 |
| <b>c</b>             | 0.10 | 0.18 | 0.11 |
| <b>D</b>             | 1.50 | 1.70 | 1.60 |
| <b>E</b>             | 1.55 | 1.70 | 1.60 |
| <b>E1</b>            | 1.10 | 1.25 | 1.20 |
| <b>e</b>             | --   | --   | 0.50 |
| <b>e1</b>            | 0.90 | 1.10 | 1.00 |
| <b>L</b>             | 0.10 | 0.30 | 0.20 |
| <b>a</b>             | 8°   | 9°   | 7°   |
| All Dimensions in mm |      |      |      |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| <b>C</b>   | 0.500         |
| <b>C1</b>  | 1.270         |
| <b>G</b>   | 0.600         |
| <b>X</b>   | 0.300         |
| <b>X1</b>  | 1.300         |
| <b>Y</b>   | 0.670         |
| <b>Y1</b>  | 1.940         |

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